



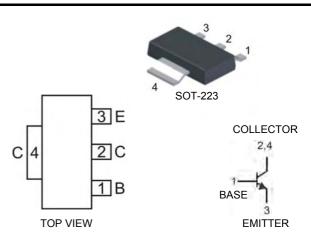
# **DZT3150** NPN SURFACE MOUNT TRANSISTOR

#### Features

- Epitaxial Planar Die Construction •
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

### **Mechanical Data**

- Case: SOT-223 •
- Case Material: Molded Plastic, "Green" Molding Compound. • UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C •
- Terminals: Finish Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.115 grams (approximate)



Schematic and Pin Configuration

#### Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
Collector-Base Voltage	V <sub>CBO</sub>	50	V	
Collector-Emitter Voltage	V <sub>CEO</sub>	25	V	
Emitter-Base Voltage	V <sub>EBO</sub>	7.0	V	
Collector Current	Ι <sub>C</sub>	5.0	А	
Base Current	Ι <sub>Β</sub>	1.0	А	
Power Dissipation	P <sub>D</sub>	1 (Note 3) 2 (Note 4)	W	
Thermal Resistance, Junction-to-Ambient	R <sub>eJA</sub>	125 (Note 3) 62.5 (Note 4)	°C/W	
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-65 to +150	°C	

Notes: 1.

No purposefully added lead. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php. Device mounted on FR-4 PCB, pad layout as shown on page 4. Device mounted on Polyimide PCB with a copper area of 1.8cm<sup>2</sup>. 2.

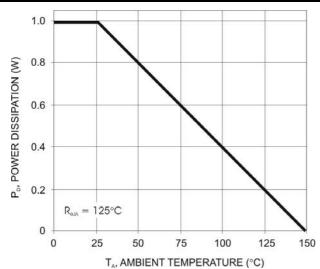
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4.



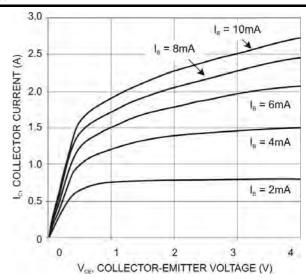
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	25			V	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0$
Collector Cutoff Current	I <sub>CBO</sub>	_		1.0	μA	$V_{CB} = 50V, I_E = 0$
Emitter Cutoff Current	I <sub>EBO</sub>	_	_	1.0	μA	$V_{EB} = 7.0V, I_{C} = 0$
ON CHARACTERISTICS						
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_		0.35 0.50	V V	$I_{C} = 3.0A, I_{B} = 150mA^{*}$ $I_{C} = 4.0A, I_{B} = 200mA^{*}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	_	—	1.10 1.40	V V	$I_{C} = 3.0A, I_{B} = 150mA^{*}$ $I_{C} = 4.0A, I_{B} = 200mA^{*}$
DC Current Gain	h <sub>FE</sub>	250 150 50	_	500 —	_	$ \begin{array}{l} I_{C} = 500 \text{mA},  V_{CE} = 2.0 \text{V}^{\star} \\ I_{C} = 2.0 \text{A},  V_{CE} = 2.0 \text{V}^{\star} \\ I_{C} = 5.0 \text{A},  V_{CE} = 2.0 \text{V}^{\star} \end{array} $
SMALL SIGNAL CHARACTERISTICS	· · ·					
Current Gain-Bandwidth Product	f <sub>T</sub>		150		MHz	$I_{C} = 50$ mA, $V_{CE} = 6.0$ V, f = 200MHz
Output Capacitance	C <sub>obo</sub>	_	_	50	pF	$V_{CB} = 10V, I_{F} = 0, f = 1MHz$

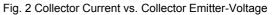
\* Measured under pulsed conditions. Pulse width =  $300\mu s$ . Duty cycle  $\leq 2\%$ 



# Typical Characteristics @T<sub>amb</sub> = 25°C unless otherwise specified

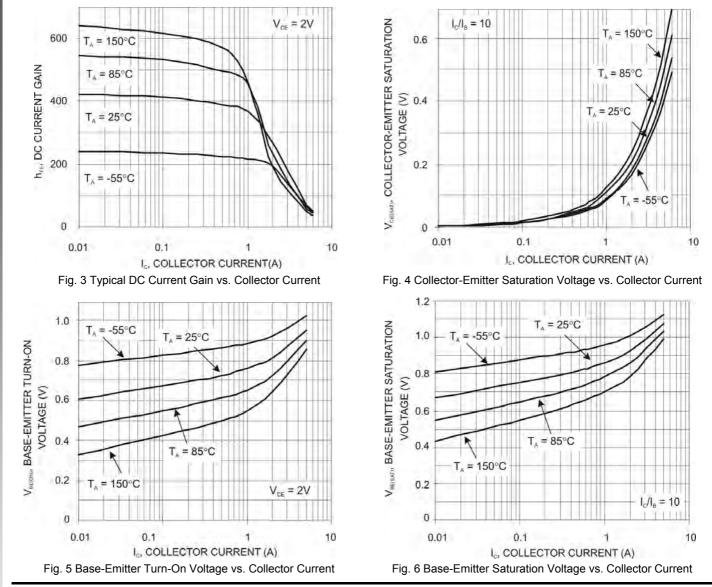








**NEW PRODUCT** 



#### Ordering Information (Note 5)

Device	Packaging	Shipping
DZT3150-13	SOT-223	2500/Tape & Reel

Notes: 5. Packaging Details as shown on page 4, or go to our website at http://www.diodes.com/ap2007.pdf.

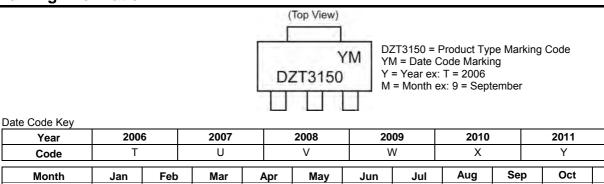
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#### **Marking Information**



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Code

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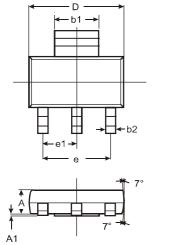
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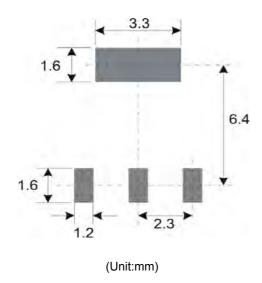
### **Package Outline Dimensions**



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	Ė ⊑1
0° -	10°
0	

SOT-223				
Dim	Min	Мах	Тур	
Α	1.55	1.65	1.60	
A1	0.010	0.15	0.05	
b1	2.90	3.10	3.00	
b2	0.60	0.80	0.70	
С	0.20	0.30	0.25	
D	6.45	6.55	6.50	
Е	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
e	_	_	4.60	
e1	_	_	2.30	
L	0.85	1.05	0.95	
Q	0.84	0.94	0.89	
All Dimensions in mm				

## Suggested Pad Layout: (Based on IPC-SM-782)



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